

39th IEEE Semiconductor Interface Specialists Conference (SISC) to Be Held in December 2008

www.ieeesisc.org

The 39th IEEE Semiconductor Interface Specialists Conference (SISC) will be held December 11–13, 2008, at the Catamaran Resort Hotel in San Diego, California. The SISC provides a forum for materials researchers, solid-state physicists, and device engineers to discuss issues related to semiconductor/insulator interfaces, the physics of insulating thin films, and the interaction among materials science, device physics, and state-of-the-art technology. Emphasis is on transistor and memory devices incorporating high-*k* gate dielectrics and metal gate electrodes on silicon and on high-carrier-mobility substrates.

The 39th SISC is organized by Ben Kaczer, General Chair (IMEC); Dina Triyoso, Technical Chair (Freescale Semiconductor); and Martin M. Frank, Arrangements Chair (IBM Research). Confirmed invited speakers include A. Demkov (University of Texas, Austin), P. McIntyre (Stanford University), V. Narayanan (IBM Research), and A. Toriumi (University of Tokyo).

The abstract submission deadline is July 25, 2008.

Together with oral sessions of invited and contributed talks as well as a poster session, this year's SISC will continue the

tradition of presenting a Best Student Presentation award, established in memory of E.H. Nicollian, a pioneer in the exploration of the metal-oxide-semiconductor system.

SISC is sponsored by the IEEE Electron Devices Society, and the Materials Research Society (MRS) has cooperating status.

Further details, including contact information and previous technical programs, can be obtained from the conference Web site www.ieeesisc.org.

MARTIN M. FRANK

IBM T. J. Watson Research Center
Arrangements Chair of the 39th IEEE SISC

6th International Conference on High-Temperature Capillarity to Be Held in May 2009

www.htc2009.org

The 6th International Conference on High-Temperature Capillarity (HTC-2009) will be held May 6–9, 2009 in Athens, Greece. The conference will address issues linked to surfaces and interfaces, wetting, and capillarity phenomena specifically related to materials as well as to materials processing at elevated temperatures. The conference will particularly focus on surfaces and interfaces of metals, ceramics and glasses, wetting of surfaces and grain boundaries, and capillarity in materials processing.

HTC-2009 is chaired by Nicolas Eustathopoulos, Program Chair (Labora-

toire de Thermodynamique et Physico-chimie Métallurgique, Grenoble, France) and Panagiotis Nikolopoulos, Chair of the Local Organizing Committee (University of Patras, Greece).

The abstract submission deadline is September 30, 2008.

The official language of the conference is English. Proceedings of the conference, after peer-review, will be published in a special issue of *Interface Science*, now part of the *Journal of Materials Science*.

The conference is organized by the University of Patras, Chemical Engineering Department, Greece and the

University of Ioannina, Materials Science and Engineering Department, Greece; co-organized by the Joining and Welding Research Institute, Osaka University, Japan; and sponsored by the organizers as well as the University of Alicante, Spain.

For more information, contact Secretariat S. Agathopoulos, Materials Science and Engineering Department, University of Ioannina, GR-451 10, Ioannina, Greece; tel. 30-265109-7381; fax 30-265109-7074; e-mail sagat@cc.uoi.gr; or access the Web site at www.htc2009.org. □